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August 2016

Single-Channel: 6N138M, 6N139M Dual-Channel: HCPL2730M, HCPL2731M 8-Pin DIP Low Input Current High Gain Split Darlington Optocouplers

Features

- Low Current 0.5 mA
- Superior CTR 2000%
- Superior CMR 10 kV/µs
- CTR Guaranteed 0 to 70°C
- Dual Channel HCPL2730M, HCPL2731M
- · Safety and Regulatory Approvals
 - UL1577, 5,000 VAC_{RMS} for 1 Minute
 - DIN EN/IEC60747-5-5

Applications

- · Digital Logic Ground Isolation
- Telephone Ring Detector
- EIA-RS-232C Line Receiver
- High Common Mode Noise Line Receiver
- µP Bus Isolation
- Current Loop Receiver

Description

The single-channel, 6N138M, 6N139M and dual-channel HCPL2730M, HCPL2731M optocouplers consist of an AlGaAs LED optically coupled to a high gain split darlington photodetector.

The split darlington configuration separating the input photodiode and the first stage gain from the output transistor permits lower output saturation voltage and higher speed operation than possible with conventional darlington phototransistor optocoupler. In the dual channel devices, HCPL2730M and HCPL2731M, an integrated emitter-base resistor provides superior stability over temperature.

The combination of a very low input current of 0.5 mA and a high current transfer ratio of 2000% makes this family particularly useful for input interface to MOS, CMOS, LSTTL and EIA RS232C, while output compatibility is ensured to CMOS as well as high fan-out TTL requirements. An internal noise shield provides exceptional common mode rejection of 10 kV/µs.

Related Resources

- <u>www.fairchildsemi.com/products/optoelectronics/</u>
- <u>www.fairchildsemi.com/pf/HC/HCPL0700.html</u>
- <u>www.fairchildsemi.com/pf/HC/HCPL0730.html</u>
 - www.fairchildsemi.com/pf/HC/HCPL0731.html

Schematics

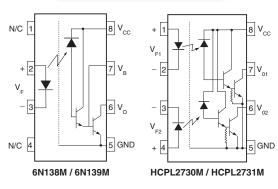


Figure 1. Schematics

Package Outlines

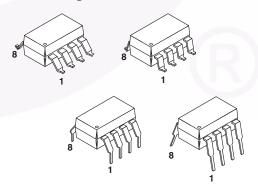


Figure 2. Package Options

Safety and Insulation Ratings

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter	Characteristics	
	< 150 V _{RMS}	I–IV
	< 300 V _{RMS}	I–IV
Installation Classifications per DIN VDE 0110/1.89 Table 1, For Rated Mains Voltage	< 450 V _{RMS}	I–III
	< 600 V _{RMS}	I–III
	< 1,000 V _{RMS} (Option T, TS)	1-111
Climatic Classification		40/100/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
V	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$, Type and Sample Test with t _m = 10 s, Partial Discharge < 5 pC	2,262	V _{peak}
V _{PR}	Input-to-Output Test Voltage, Method B, $V_{IORM} \times 1.875 = V_{PR}$, 100% Production Test with $t_m = 1 \text{ s}$, Partial Discharge < 5 pC	2,651	V _{peak}
VIORM	Maximum Working Insulation Voltage	1,414	V _{peak}
V _{IOTM}	Highest Allowable Over-Voltage	6,000	V _{peak}
	External Creepage	≥ 8.0	mm
	External Clearance	≥ 7.4	mm
	External Clearance (for Option TV, 0.4" Lead Spacing)	≥ 10.16	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.5	mm
Τ _S	Case Temperature ⁽¹⁾	150	°C
I _{S,INPUT}	Input Current ⁽¹⁾	200	mA
P _{S,OUTPUT}	Output Power (Duty Factor $\leq 2.7\%$) ⁽¹⁾	300	mW
R _{IO}	Insulation Resistance at T _S , V_{IO} = 500 $V^{(1)}$	> 10 ⁹	Ω

Note:

1. Safety limit value - maximum values allowed in the event of a failure.

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. $T_A = 25^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Value	Unit
T _{STG}	Storage Temperature	-40 to +125	°C
T _{OPR}	Operating Temperature	-40 to +100	°C
TJ	Junction Temperature	-40 to +125	°C
T _{SOL}	Lead Solder Temperature	260 for 10 sec	°C

Symbol	Parameter	Device	Value	Unit
EMITTER				
l _F (avg)	DC/Average Forward Input Current Per Channel	All	20	mA
l _F (pk)	Peak Forward Input Current Per Channel (50% duty cycle, 1 ms P.W.)	All	40	mA
I _F (trans)	Peak Transient Input Current Per Channel (≤ 1 µs P.W., 300 pps)	All	1	А
V _R	Reverse Input Voltage Per Channel	All	5	V
PD	Input Power Dissipation Per Channel ⁽²⁾	All	35	mW
DETECTOR	· /			
l _O (avg)	Average Output Current Per Channel	All	60	mA
V _{ER}	Emitter-Base Reverse Voltage	6N138M, 6N139M	0.5	V
M M	Supply Voltage Output Voltage	6N138M, HCPL2730M	-0.5 to 7.0	V
V _{CC} , V _O	Supply Voltage, Output Voltage	6N139M, HCPL2731M	-0.5 to 18.0	V
Po	Output Power Dissipation Per Channel	All	100	mW

Note:

2. No derating required for devices operated within the T_{OPR} specification (6N138M and 6N139M only).

6N138M, 6N139M, HCPL2730M, HCPL2731M — 8-Pin DIP Low Input Current High Gain Split Darlington Optocouplers

Individual Component Characteristics

(V_{CC} = 5.0 V, T_A = 0°C to 70°C unless otherwise specified. Typical value is measured at T_A = 25°C.)

Symbol	Parameter	Device	Test Conditions	Min.	Тур.	Max.	Unit
EMITTER				•	•	•	
N/		A.II.	I _F = 1.6 mA, T _A = 25°C		1.30	1.70	
V_{F}	Input Forward Voltage	All	I _F = 1.6 mA			1.75	V
BV _R	Input Reverse Breakdown Voltage	All	I _R = 10 μA, T _A = 25°C	5.0	19.0		V
$\Delta V_{F} / \Delta T_{A}$	Temperature Coefficient of Forward Voltage	All	I _F = 1.6 mA		-1.94		mV/°0
DETECTO	R				•		
	Logic Low Supply	6N138M, 6N139M	I_F = 1.6 mA, V _O = Open, V _{CC} = 18 V		0.4	1.5	
I _{CCL}	Current	HCPL2730M	$V_{CC} = 7 V$ $I_{F1} = I_{F2} = 1.6 mA,$		4.05	~	mA
		HCPL2731M	$V_{CC} = 18 V$ $V_{O1} = V_{O2} = Open$		1.25	3	
	Logic High Supply	6N138M, 6N139M	I _F = 0 mA, V _O = Open, V _{CC} = 18 V		0.0003	10	_
Гссн	Current		$V_{CC} = 7 V$ $I_{F1} = I_{F2} = 0 mA,$ $V_{CC} = 18 V$ $V_{O1} = V_{O2} = Open$		0.0003	20	μA
Tranafar (Characteristics					l	
Symbol	Parameter	Device	Test Conditions	Min.	Тур.	Max.	Unit
COUPLED		Device	Test conditions		тур.		
		6N138M HCPL2730M	I _F = 1.6 mA, V _O = 0.4 V, V _{CC} = 4.5 V	300	1600 2400	_	
CTR	Current Transfer Ratio ⁽³⁾⁽⁴⁾	6N139M HCPL2731M	I _F = 0.5 mA, V _O = 0.4 V, V _{CC} = 4.5 V	400	2000 3500	-	%
		6N139M HCPL2731M	I _F = 1.6 mA, V _O = 0.4 V,	500	1600 2400		
	Logic High Output	6N138M HCPL2730M	I _F = 0 mA, V _O = V _{CC} = 7 V		0.001	250	Γ.
I _{ОН}	Current	6N139M HCPL2731M	I _F = 0 mA, V _O = V _{CC} = 18 V		0.0036	100	- μΑ
		6N138M HCPL2730M	I _F = 1.6 mA, I _O = 4.8 mA, V _{CC} = 4.5 V		0.06	0.4	
		6N139M	$I_F = 0.5 \text{ mA}, I_O = 2 \text{ mA}, V_{CC} = 4.5 \text{ V}$		0.05	0.4	
V _{OL}	Logic Low Output Volt- age ⁽⁴⁾	6N139M HCPL2731M	I _F = 1.6 mA, I _O = 8 mA, V _{CC} = 4.5 V		0.093 0.08	0.4	v
		6N139M HCPL2731M	I _F = 5 mA, I _O = 15 mA, V _{CC} = 4.5 V		0.13	0.4	P
					1	1	-

Notes:

Current Transfer Ratio is defined as a ratio of output collector current, I_O, to the forward LED input current, I_F, times 100%.

4. Pin 7 open. (6N138M and 6N139M only)

Electrical Characteristics (Continued)

(V_{CC} = 5.0 V, T_A = 0°C to 70°C unless otherwise specified. Typical value is measured at T_A = 25°C.)

Switching Characteristics

Symbol	Parameter	Device	Test Conditions	Min.	Тур.	Max.	Unit
		6N139M	R _L = 270 Ω, I _F = 12 mA		0.2	2	
		HCPL2730M, HCPL2731M	R _L = 270 Ω, I _F = 12 mA		0.5	3	
÷	Propagation Delay	6N138M	R _L = 2.2 kΩ, I _F = 1.6 mA		1.0	15	
t _{PHL}	Time to Logic LOW ⁽⁴⁾ (Fig. 15)	HCPL2730M, HCPL2731M	R _L = 2.2 kΩ, I _F = 1.6 mA		2.5	25	μs
		6N139M	R _L = 4.7 kΩ, I _F = 0.5 mA		2.5	30	
		HCPL2731M	R _L = 4.7 kΩ, I _F = 0.5 mA		8.4	120	
		6N139M	R _L = 270 Ω, I _F = 12 mA		1.3	10	
	Draman tian Dalau	HCPL2730M, HCPL2731M	R _L = 270 Ω, I _F = 12 mA		1.0	15	
t _{PLH}	Propagation Delay Time to Logic HIGH ⁽⁴⁾ (Fig. 15)	6N138M, HCPL2730M, HCPL2731M	R _L = 2.2 kΩ, I _F = 1.6 mA		7.3	50	μs
		6N139M, HCPL2731M	R _L = 4.7 kΩ, I _F = 0.5 mA		13.6	90	
CM _H	Common Mode Transient Immunity at Logic High ⁽⁵⁾ (Fig. 16)	All	I _F = 0 mA, IV _{CM} I = 10 V _{P-P} R _L = 2.2 kΩ, T _A = 25°C	1,000	10,000		V/µs
CM _L	Common Mode Transient Immunity at Logic Low ⁽⁵⁾ (Fig. 16)	All	I _F = 1.6 mA, IV _{CM} I = 10 V _{P-P} , R _L = 2.2 kΩ, T _A = 25°C	1,000	10,000		V/µs

Note:

5. Common mode transient immunity in logic HIGH level is the maximum tolerable (positive) dV_{cm}/dt on the leading edge of the common mode pulse signal V_{CM} , to assure that the output will remain in a logic HIGH state (i.e., $V_O > 2.0 V$). Common mode transient immunity in logic LOW level is the maximum tolerable (negative) dV_{cm}/dt on the trailing edge of the common mode pulse signal, V_{CM} , to assure that the output will remain in a logic LOW level is the maximum tolerable (negative) dV_{cm}/dt on the trailing edge of the common mode pulse signal, V_{CM} , to assure that the output will remain in a logic LOW state (i.e., $V_O < 0.8 V$).

Electrical Characteristics (Continued)

Symbol	Parameter	Device	Test Conditions	Min.	Тур.	Max.	Unit
V _{ISO}	Withstand Insulation Test Voltage ⁽⁶⁾⁽⁷⁾	All	$\begin{array}{l} RH \leq 50\%, \ T_A = 25^{\circ}C, \\ I_{I-O} \leq 10 \ \mu\text{A}, \ t = 1 \ min, \\ f = 50 \ Hz \end{array}$	5,000			VAC _{RMS}
R _{I-O}	Resistance (Input to Output) ⁽⁶⁾	All	V _{I-O} = 500 V _{DC}		10 ¹¹		Ω
C _{I-O}	Capacitance (Input to Output) ⁽⁶⁾⁽⁸⁾	All	f = 1 MHz, V _{I-O} = 0 V		1		pF
I _{I-I}	Input-Input Insulation Leakage Current ⁽⁹⁾	HCPL2730M, HCPL2731M	$\label{eq:RH} \begin{array}{l} RH \leq 45\%, V_{\text{I-I}} = 500 V_{DC}, \\ t = 5 \text{sec} \end{array}$		0.005		μA
R _{I-I}	Input-Input Resistance ⁽⁹⁾	HCPL2/31W	$v_{I-I} = 500 v_{DC}$		10 ¹¹		Ω
C _{I-I}	Input-Input Capacitance ⁽⁹⁾	HCPL2730M, HCPL2731M	f = 1 MHz		0.03		pF

Isolation Characteristics (T_A = 25°C unless otherwise specified.)

Notes:

6. Device is considered a two terminal device: Pins 1, 2, 3 and 4 are shorted together and Pins 5, 6, 7 and 8 are shorted together.

7. 5000 VAC_{RMS} for 1 minute duration is equivalent to 6000 VAC_{RMS} for 1 second duration.

8. For dual channel devices, C_{I-O} is measured by shorting pins 1 and 2 or pins 3 and 4 together and pins 5 through 8 shorted together.

9. Measured between pins 1 and 2 shorted together, and pins 3 and 4 shorted together.

Electrical Characteristics (Continued)

 $T_A = 25^{\circ}C$ unless otherwise specified

Current Limiting Resistor Calculations: R_1 (Non-Invert) = V_{CC1} - V_{DF} - V_{OL1} I_F

 $R_1 \text{ (Invert)} = V_{CC1} - V_{OH1} - V_{DF}$

$$R_2 = V_{CC2} - V_{OLX} (@ I_L - I_2)$$

 I_1

INPUT				R ₂ (Ω) @ OUT	PUT CO	NFIGUR	ATION								
-	URATION	R ₁ (Ω)	CMOS @ 5 V	CMOS @ 10 V	74XX	74LXX	74SXX	74LSXX	74HXX							
смоѕ	NON-INV.	2000														
@ 5 V	INV.	510														
смоѕ	NON-INV.	5100														
@ 10 V	INV.	4700														
	NON-INV.	2200														
74XX	INV.	180														
	NON-INV.	1800		1000	1000								750	1000		
74LXX	INV.	100	1000	2200	0 750 1000	1000	00 1000	1000	560							
-	NON-INV.	2000														
74SXX	INV.	360														
	NON-INV.	2000														
74LSXX	INV.	180														
741177	NON-INV.	2000														
74HXX	INV.	180														

Where: V_{CC1} = Input Supply Voltage

$$\begin{split} V_{DF} &= \text{Diode Forward Voltage} \\ V_{OL1} &= \text{Logic "0" Voltage of Driver} \\ V_{OH1} &= \text{Logic "1" Voltage of Driver} \\ I_F &= \text{Diode Forward Current} \\ V_{OLX} &= \text{Saturation Voltage of} \\ Output Transistor \\ I_L &= \text{Load Current Through} \\ \text{Resistor } R_2 \end{split}$$

V_{CC2} = Output Supply Voltage

I₂ = Input Current of Output Gate

Fig. 3 Resistor Values for Logic Interface

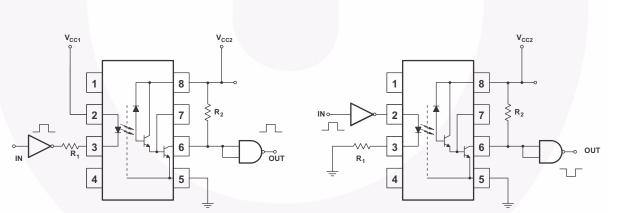
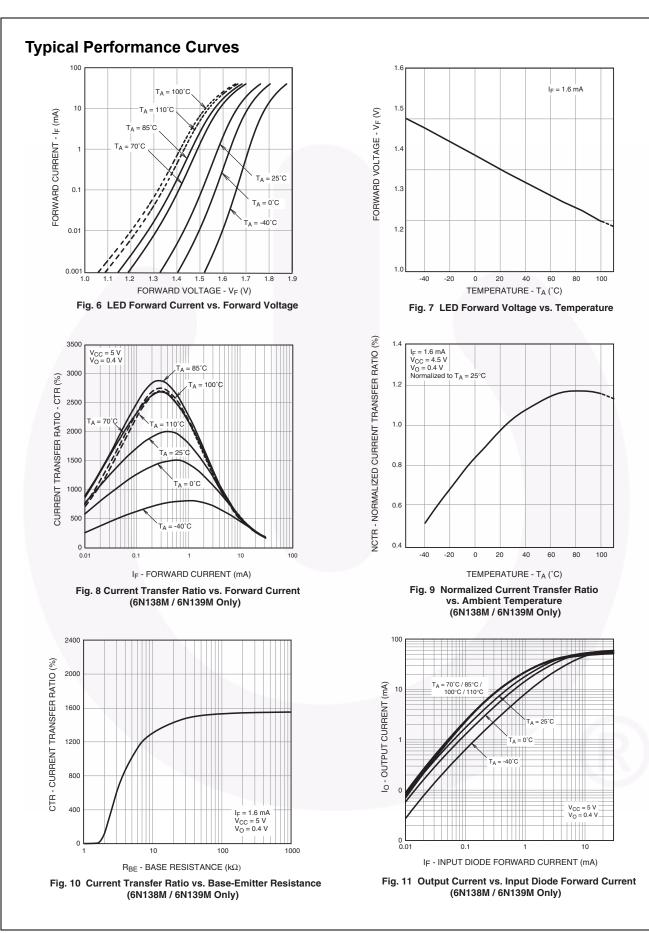
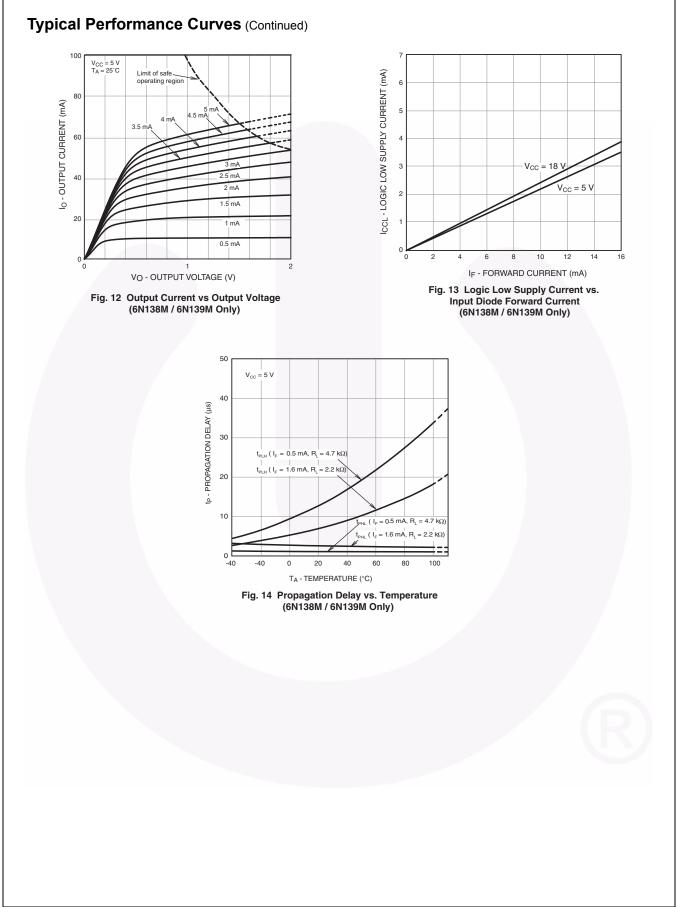
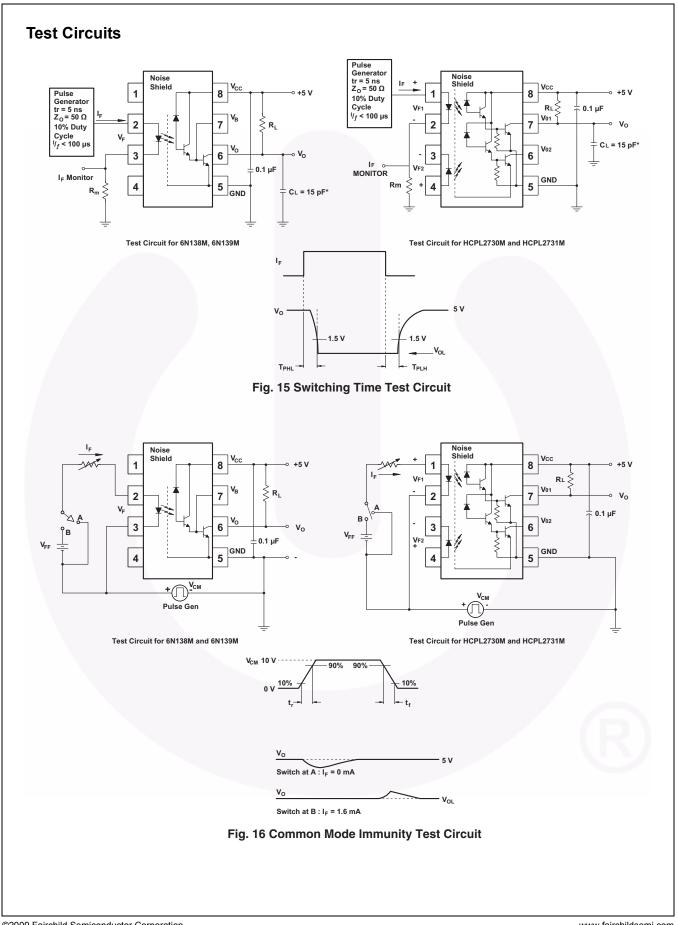


Fig. 4 Non-Inverting Logic Interface ig 5 Inverting Logic In Fig. 5 Inverting Logic Interface

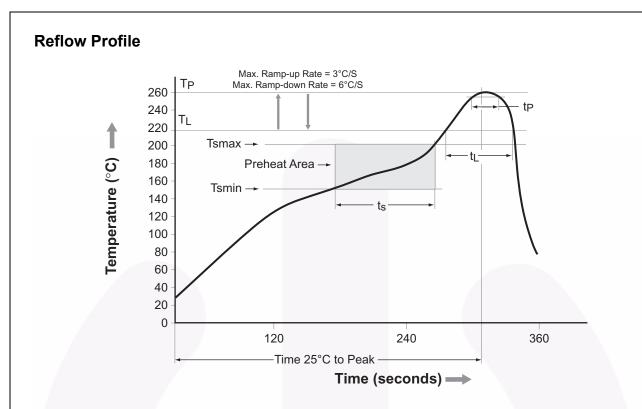








6N138M, 6N139M, HCPL2730M, HCPL2731M — 8-Pin DIP Low Input Current High Gain Split Darlington Optocouplers



Profile Freature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (t _S) from (Tsmin to Tsmax)	60–120 seconds
Ramp-up Rate (t _L to t _P)	3°C/second max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60–150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of 260°C	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.

Ordering Information

Part Number	Package	Packing Method
6N138M	DIP 8-Pin	Tube (50 units per tube)
6N138SM	SMT 8-Pin (Lead Bend)	Tube (50 units per tube)
6N138SDM	SMT 8-Pin (Lead Bend)	Tape and Reel (1,000 units per reel)
6N138VM	DIP 8-Pin, DIN EN/IEC 60747-5-5 Option	Tube (50 units per tube)
6N138SVM	SMT 8-Pin (Lead Bend), DIN EN/IEC 60747-5-5 Option	Tube (50 units per tube)
6N138SDVM	SMT 8-Pin (Lead Bend), DIN EN/IEC 60747-5-5 Option	Tape and Reel (1,000 units per reel)
6N138TVM	DIP 8-Pin, 0.4" Lead Spacing, DIN EN/IEC 60747-5-5 Option	Tube (50 units per tube)
6N138TSVM	SMT 8-Pin, 0.4" Lead Spacing, DIN EN/IEC 60747-5-5 Option	Tube (50 units per tube)
6N138TSR2VM	SMT 8-Pin, 0.4" Lead Spacing, DIN EN/IEC 60747-5-5 Option	Tape and Reel (1,000 units per reel)

Note:

The product orderable part number system listed in this table also applies to the 6N139M, HCPL2730M and HCPL2731M product families.

Marking Information

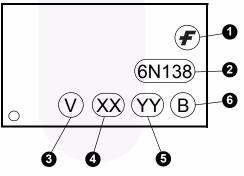
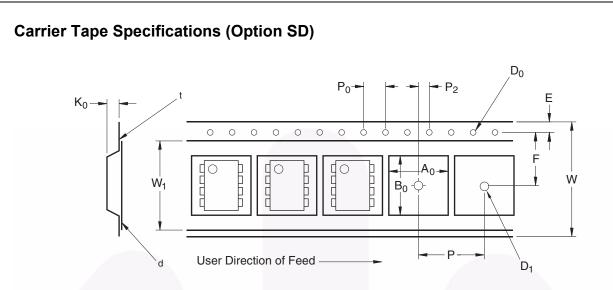
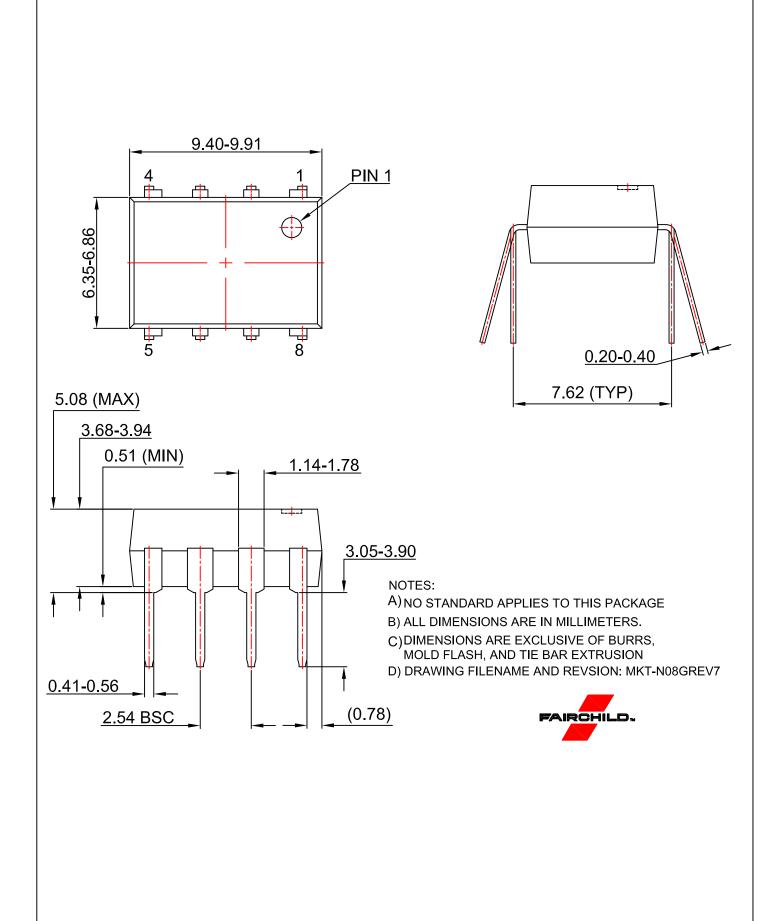


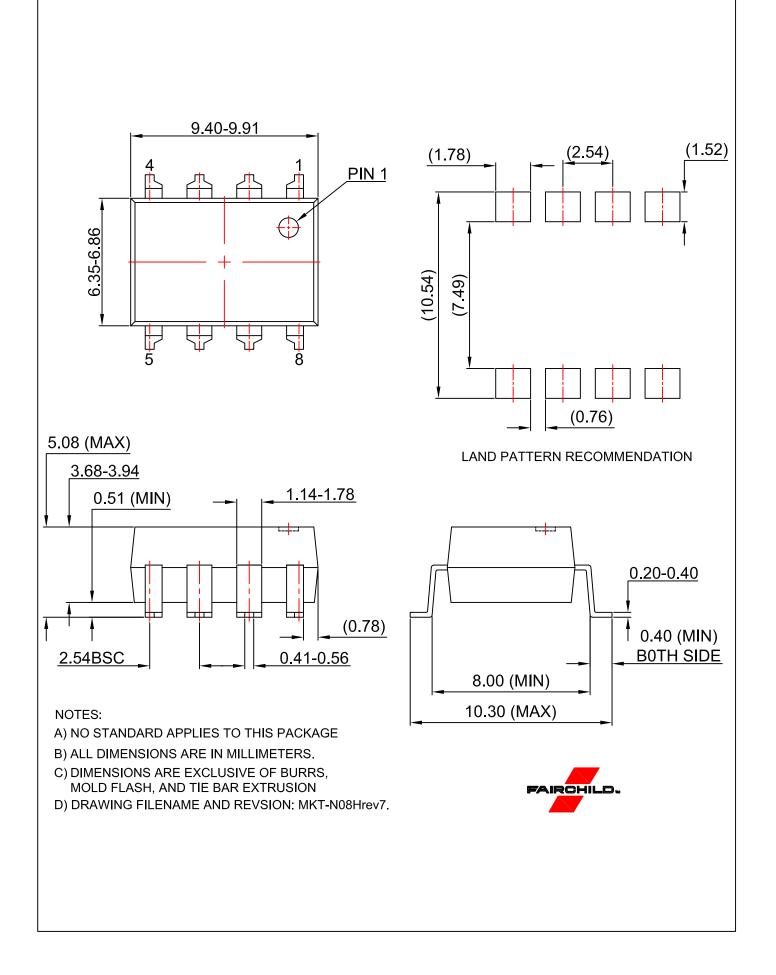
Figure 17. Top Mark

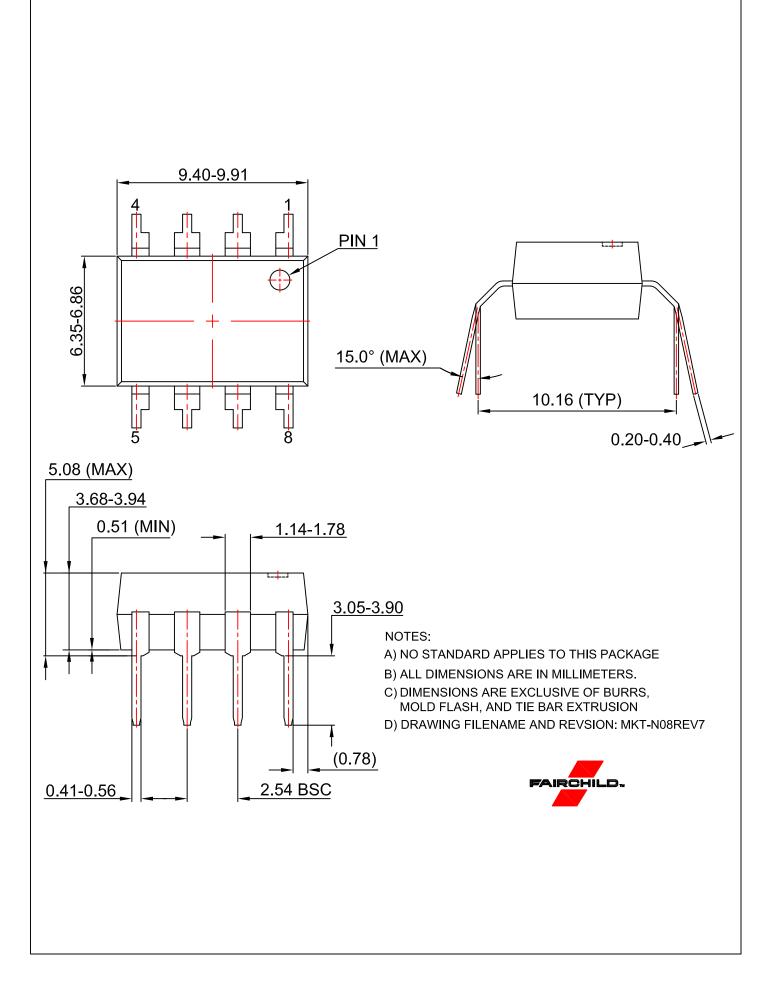
Defini	Definitions			
1	Fairchild Logo			
2	Device Number			
3	DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)			
4	Two Digit Year Code, e.g., '16'			
5	Two Digit Work Week Ranging from '01' to '53'			
6	Assembly Package Code			



Symbol	Description	Dimension in mm
W	Tape Width	16.0 ± 0.3
t	Tape Thickness	0.30 ± 0.05
P ₀	Sprocket Hole Pitch	4.0 ± 0.1
D ₀	Sprocket Hole Diameter	1.55 ± 0.05
E	Sprocket Hole Location	1.75 ± 0.10
F	Pocket Location	7.5 ± 0.1
P ₂		2.0 ± 0.1
Р	Pocket Pitch	12.0 ± 0.1
A ₀	Pocket Dimensions	10.30 ±0.20
B ₀		10.30 ±0.20
K ₀		4.90 ±0.20
W ₁	Cover Tape Width	13.2 ± 0.2
d	Cover Tape Thickness	0.1 max
	Max. Component Rotation or Tilt	10°
R	Min. Bending Radius	30







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